

## **IN THE SPECIFICATION**

*Please insert the following paragraph on page 1 after the title of the invention and before the "Technical Field":*

### **--Related Applications**

This application is a national phase of PCT/JP2005/003511 filed on March 2, 2005, which claims priority from Japanese Application No. 2004-071971 filed on March 15, 2004 and Japanese Application No. 2004-077691 March 18, 2004, the disclosures of which Applications are incorporated by reference herein. The benefit of the filing and priority dates of the International and Japanese Applications is respectfully requested.--

*The following paragraph will replace all prior versions of itself in the specification of the application.*

1) In paragraph [0030], please make the following amendment:

[0030]        Then, the second electrode forming step is performed so that the second electrode is so formed as to have an area smaller than an area occupied by the semiconductor laser layer (It is to be noted that, by the second electrode forming step, the width direction length of the second electrode may be made longer than the width direction length of the first electrode).